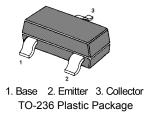
NPN Silicon General Purpose Transistor



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	V_{CBO}	60	V	
Collector Emitter Voltage	V_{CEO}	40	V	
Emitter Base Voltage	V_{EBO}	6	V	
Collector Current Continuous	I _C	600	mA	
Total Device Dissipation FR-5 Board 1)	P _{tot}	300	mW	
Thermal Resistance Junction to Ambient	$R_{ heta JA}$	417	°C/W	
Junction Temperature	T _j	150	°C	
Storage Temperature Range	T _{stg}	- 55 to + 150	°C	

¹⁾ FR-5 = 1 X 0.75 X 0.062 in.











Dated: 05/11/2015 Rev:02

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1 \text{ V}$, $I_{C} = 0.1 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_{C} = 1 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_{C} = 10 \text{ mA}$ at $V_{CE} = 1 \text{ V}$, $I_{C} = 150 \text{ mA}$ at $V_{CE} = 2 \text{ V}$, $I_{C} = 500 \text{ mA}$	h _{FE} h _{FE} h _{FE} h _{FE}	20 40 80 100 40	- - 300	- - - -
Collector Base Cutoff Current at $V_{CB} = 35 \text{ V}$	I _{CBO}	-	0.1	μΑ
Emitter Base Cutoff Current at V _{EB} = 5 V	I _{EBO}	-	0.1	μΑ
Collector Base Breakdown Voltage at I _C = 0.1mA	V _{(BR)CBO}	60	-	V
Collector Emitter Breakdown Voltage at I _C = 1 mA	V _{(BR)CEO}	40	-	V
Emitter Base Breakdown Voltage at I _E = 0.1 mA	V _{(BR)EBO}	6	-	V
Collector Emitter Saturation Voltage at I_C = 150 mA, I_B = 15 mA at I_C = 500 mA, I_B = 50 mA	$egin{array}{c} V_{\text{CE(sat)}} \ V_{\text{CE(sat)}} \end{array}$	-	0.4 0.75	>
Base Emitter Saturation Voltage at I_C = 150 mA, I_B = 15 mA at I_C = 500 mA, I_B = 50 mA	$egin{array}{c} V_{BE(sat)} \ V_{BE(sat)} \end{array}$	0.75	0.95 1.2	>
Current Gain Bandwidth Product at $V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$, $f = 100 \text{ MHz}$	f _T	250	-	MHz
Collector Base Capacitance at $V_{CB} = 5 \text{ V}$, $f = 1 \text{ MHz}$	C _{ob}	-	6.5	pF
Delay Time V_{CC} = 30 V, V_{EB} = 2 V, I_{C} = 150 mA, I_{B1} = 15 mA	t _d	-	15	ns
Rise Time $V_{CC} = 30 \text{ V}, V_{EB} = 2 \text{ V}, I_{C} = 150 \text{ mA}, I_{B1} = 15 \text{ mA}$	t _r	-	20	ns
Storage Time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = I_{B2} = 15 \text{ mA}$	t _s	-	225	ns
Fall Time $V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = I_{B2} = 15 \text{ mA}$	t _f	-	30	ns











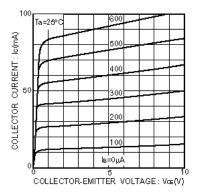


Fig.1 Grounded emitter output characteristics

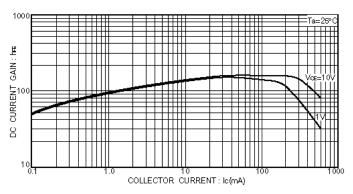


Fig.3 DC current gain vs. collector current(I)

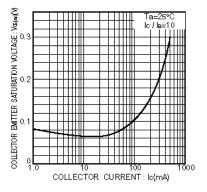


Fig.2 Collector-emitter saturation voltage vs. collector current

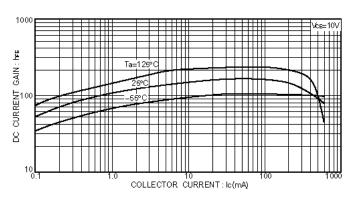


Fig.4 DC current gain vs. collector current(II)

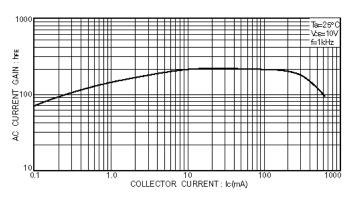


Fig.5 AC current gain vs. collector current

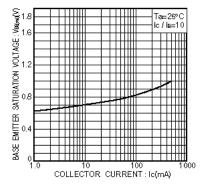


Fig.6 Base-emitter saturation voltage vs. collector current











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